

General Description

The HSU12P10 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The HSU12P10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

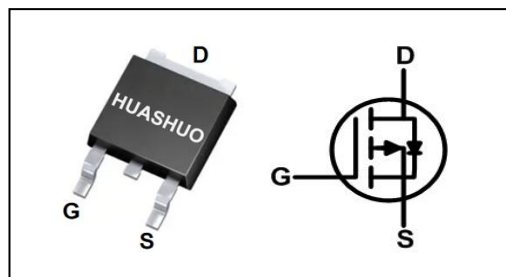
Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

Product Summary

V_{DS}	-100	V
$R_{DS(ON),Max}$	270	m Ω
I_D	-12	A

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-12	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-6.8	A
I_{DM}	Pulsed Drain Current ²	-25	A
EAS	Single Pulse Avalanche Energy ³	49	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	35	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.8	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-5A	---	240	270	mΩ
		V _{GS} =-4.5V, I _D =-5A	---	260	340	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.7	-3.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	---	---	-50	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _D =-5A	---	17	---	nC
Q _{gs}	Gate-Source Charge		---	3.13	---	
Q _{gd}	Gate-Drain Charge		---	2.7	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-30V, V _{GS} =-10V, R _G =3.3Ω, I _D =-1A	---	11	---	ns
T _r	Rise Time		---	7.4	---	
T _{d(off)}	Turn-Off Delay Time		---	39	---	
T _f	Fall Time		---	28	---	
C _{iss}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz	---	900	---	pF
C _{oss}	Output Capacitance		---	40	---	
C _{rss}	Reverse Transfer Capacitance		---	26	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

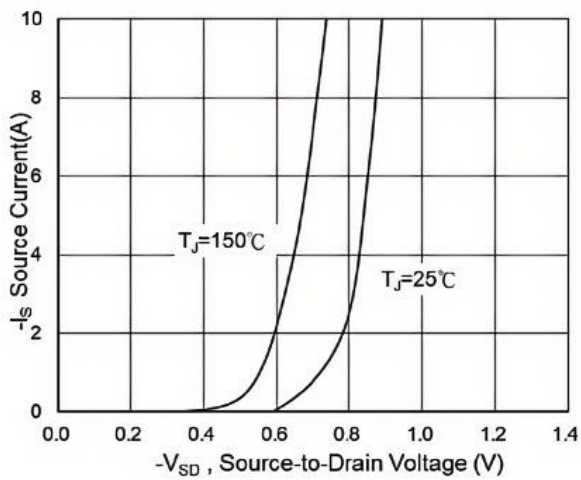


Fig.1 Typical S-D Diode Forward Voltage

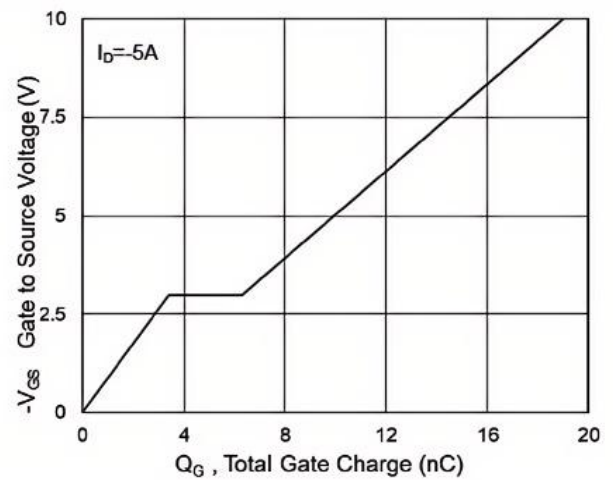
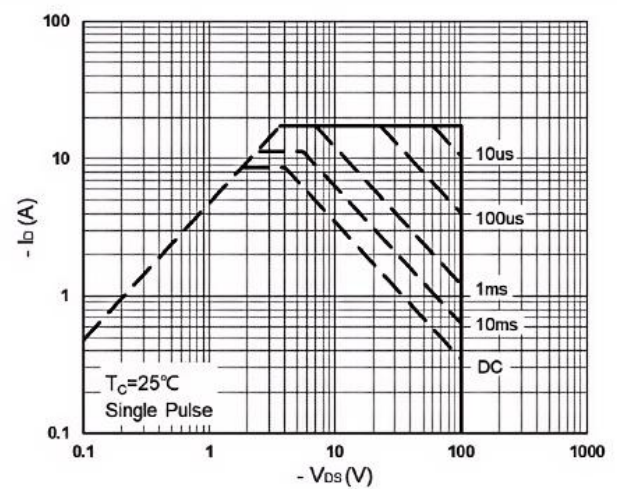
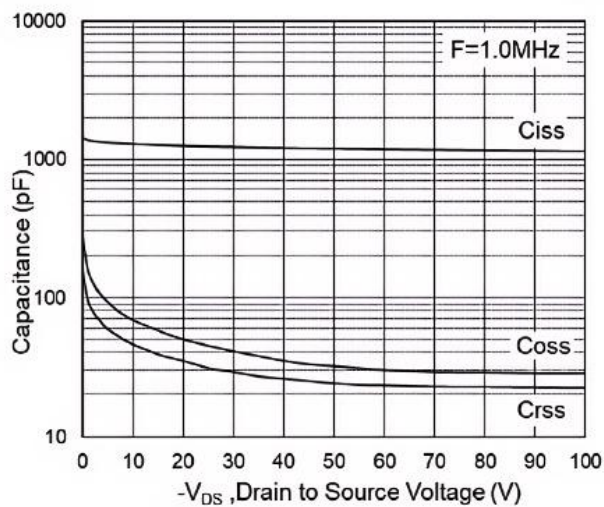
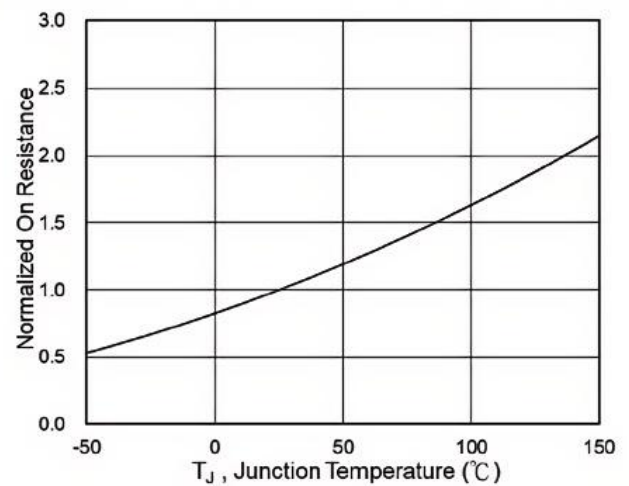
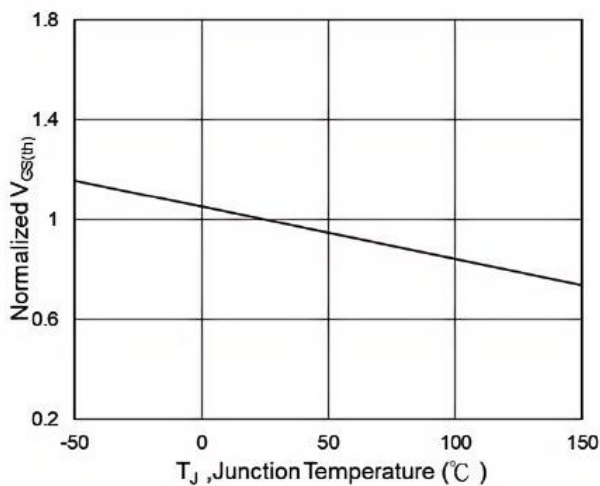


Fig.2 Gate-Charge Characteristics



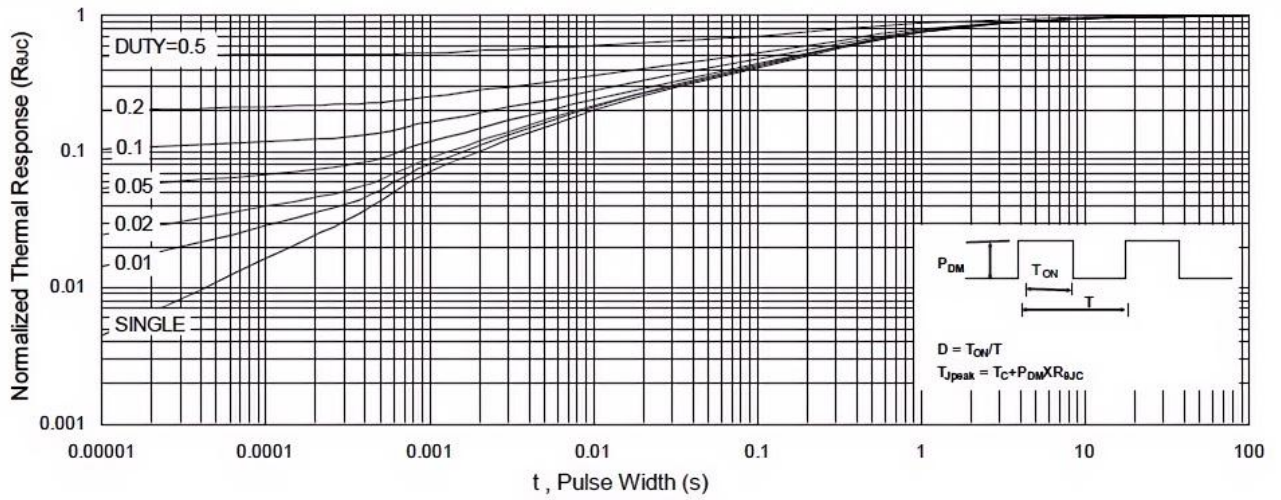


Fig.7 Normalized Maximum Transient Thermal Impedance

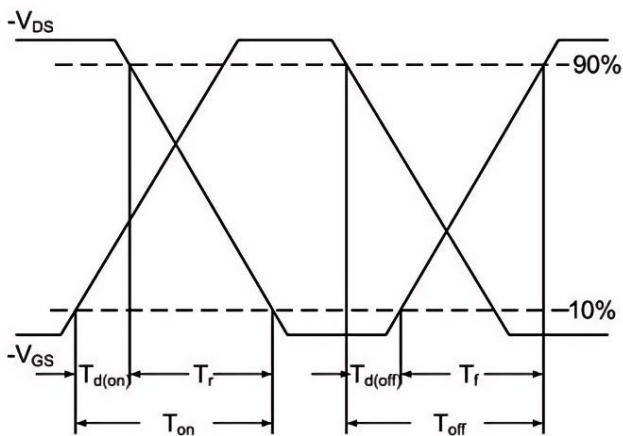


Fig.8 Switching Time Waveform

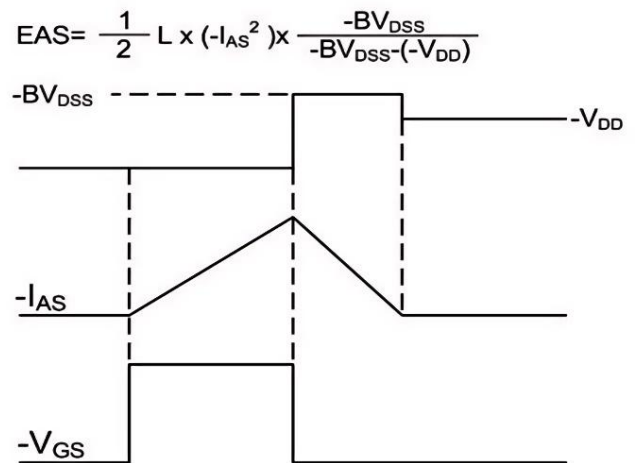


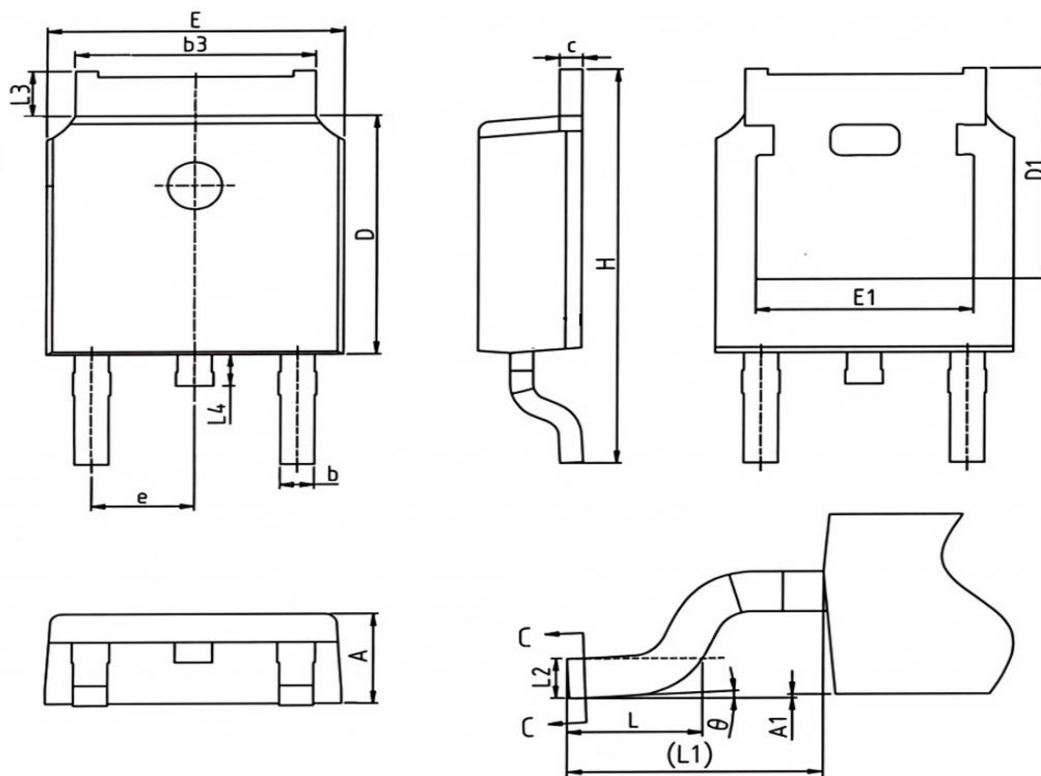
Fig.9 Unclamped Inductive Waveform



Ordering Information

Part Number	Package code	Packaging
HSU12P10	TO-252	2500/Tape&Reel

TO252 Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
C	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	---	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
θ	0°	8°	0°	8°



HSU12P10 Marking:

